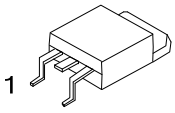
N-CHANNEL ENHANCEMENT MODE POWER MOSFET



TO-252

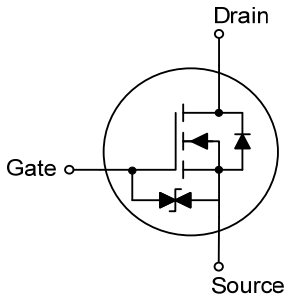
■ DESCRIPTION

This **UT8N06Z** is an N-channel power MOSFET providing very low on-resistance. It has high efficiency and perfect cost-effectiveness. It can be generally applied in the commercial and industrial fields.

■ FEATURES

* $R_{DS(ON)}$ ≤ 65 mΩ @ V_{GS}=10V, I_D=4.0A
  $R_{DS(ON)}$ ≤ 98 mΩ @ V_{GS}=4.5V, I_D=4.0A
* Fast switching capability
* Enhanced ESD capability

■ SYMBOL



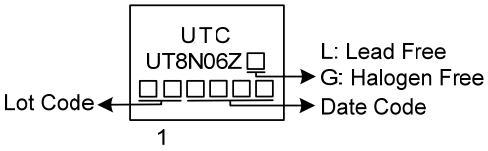
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UT8N06ZL-TN3-R	UT8N06ZG-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UT8N06ZG-TN3-R (1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATING (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous	I_D	8	A
	Pulsed (Note 2)	I_{DM}	16	A
Avalanche Energy (Note 3)	Single Pulsed (Note 3)	E_{AS}	8	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.7	V/nS
Power Dissipation		P_D	30	W
Junction Temperature		T_J	+150	°C
Storage Temperature Range		T_{STG}	-20 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. L = 0.1mH, I_{AS} = 12.6A, V_{DD}=50V, R_G = 25Ω, Starting T_J = 25°C
4. I_{SD} ≤ 8.0A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	110	°C/W
Junction to Case	θ_{JC}	4.16 (Note)	°C/W

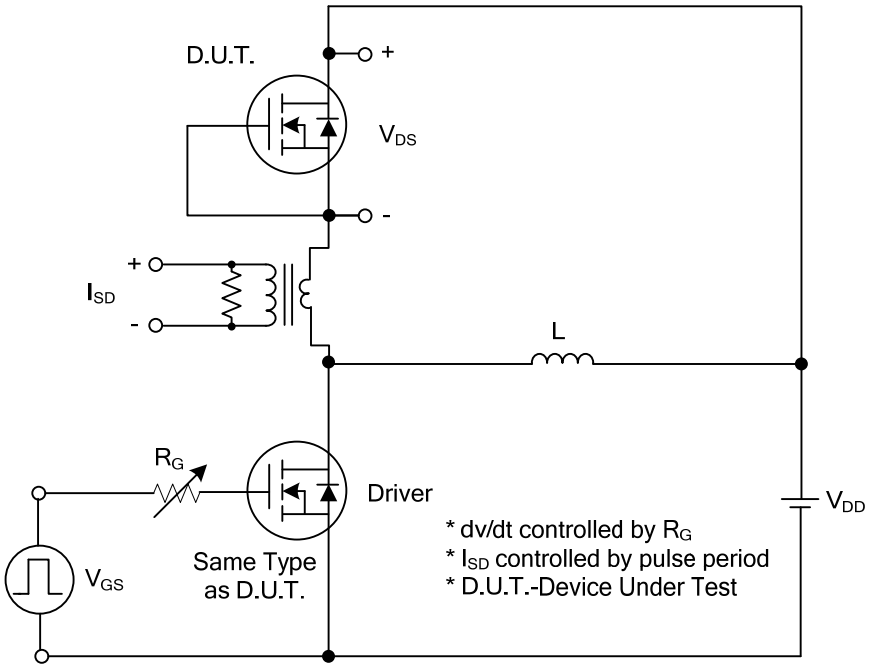
Note: The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

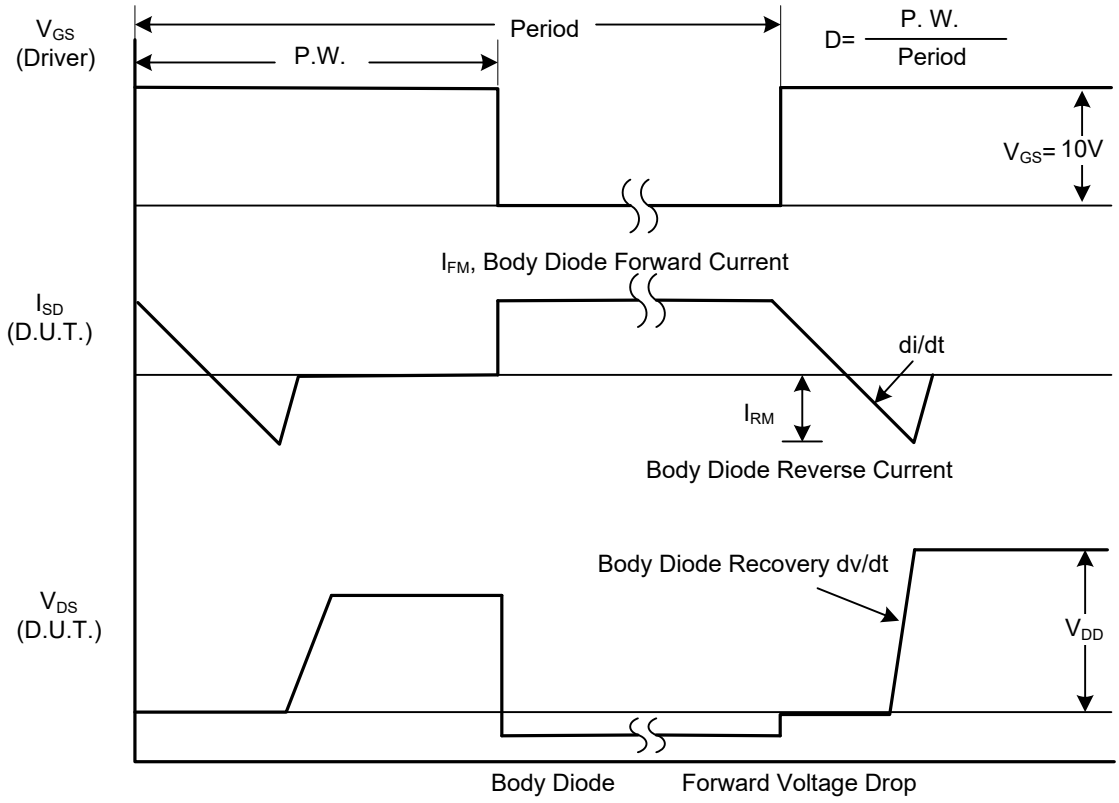
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	60			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=60V, V_{GS}=0V			1	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+20V, V_{DS}=0V			+10	μA
	Reverse		V_{GS}=-20V, V_{DS}=0V			-10	μA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	1.0		2.5	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=4.0A			65	mΩ
			V_{GS}=4.5V, I_D=4.0A			98	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		499		pF
Output Capacitance		C_{OSS}			53		pF
Reverse Transfer Capacitance		C_{RSS}			38		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q_G	V_{DS}=48V, V_{GS}=10V, I_D=8.0A (Note 1, 2)		18		nC
Gate to Source Charge		Q_{GS}			4		nC
Gate to Drain Charge		Q_{GD}			5		nC
Turn-on Delay Time (Note 1)		$t_{D(ON)}$	V_{DS}=30V, V_{GS}=10V, I_D=8.0A, R_G =3Ω (Note 1, 2)		5		ns
Rise Time		t_R			17		ns
Turn-off Delay Time		$t_{D(OFF)}$			14		ns
Fall-Time		t_F			20		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				8	A
Maximum Body-Diode Pulsed Current		I_{SM}				16	A
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	I_S=8.0A, V_{GS}=0V			1.4	V
Reverse Recovery Time (Note 1)		t_{rr}	I_S=8.0A, V_{GS}=0V, dI/dt=100A/μs		15		nS
Reverse Recovery Charge		Q_{rr}			9.5		nC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

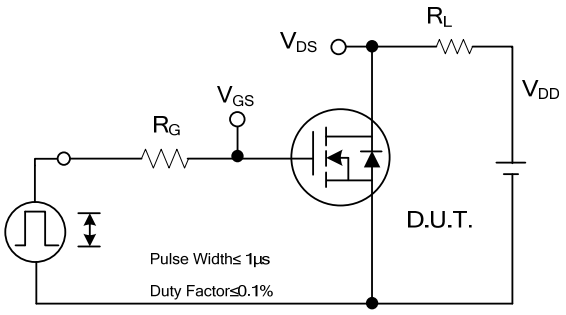


Peak Diode Recovery dv/dt Test Circuit

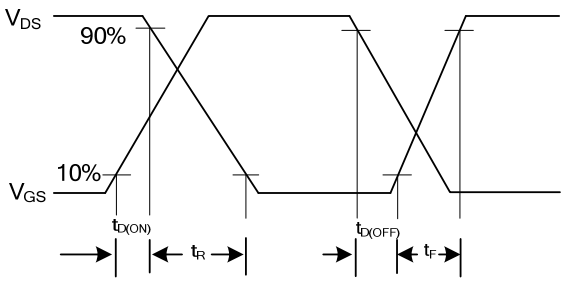


Peak Diode Recovery dv/dt Waveforms

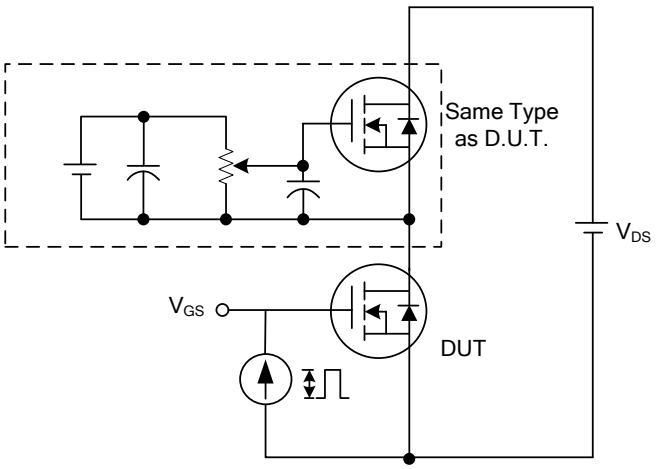
■ TEST CIRCUITS AND WAVEFORMS



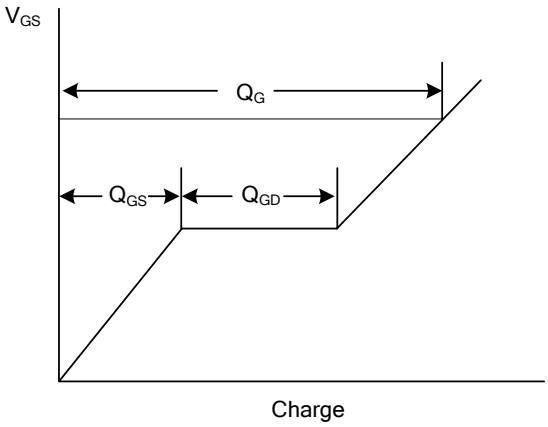
Switching Test Circuit



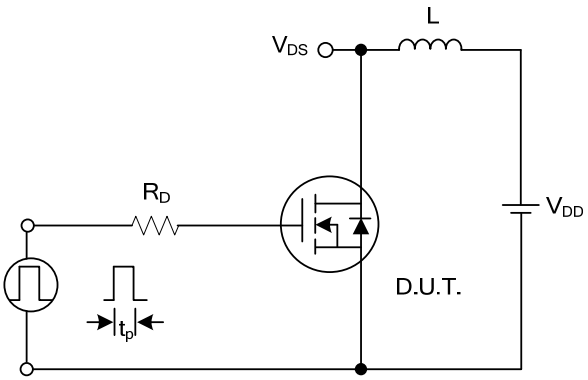
Switching Waveforms



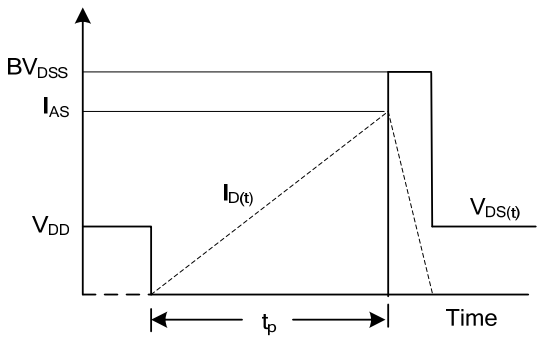
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms